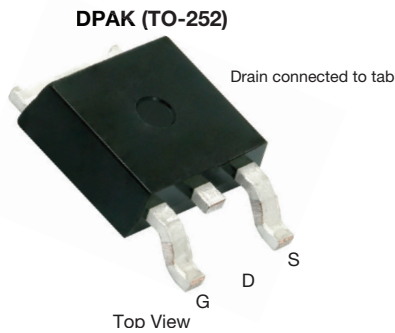
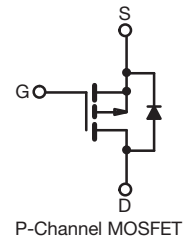


P-Channel 100 V (D-S) 175 °C MOSFET



FEATURES

- TrenchFET® Power MOSFET
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912


RoHS
COMPLIANT


| PRODUCT SUMMARY | |
|---|--------|
| V_{DS} (V) | -100 |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = -10$ V | 0.043 |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5$ V | 0.048 |
| Q_g typ. (nC) | 54 |
| I_D (A) ^a | -37 |
| Configuration | Single |

ORDERING INFORMATION

| | |
|---------------------------------|---------------------|
| Package | DPAK (TO-252) |
| Lead (Pb)-free and halogen-free | SUD50P10-43L-T1-GE3 |

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

| PARAMETER | SYMBOL | LIMIT | UNIT | |
|---|----------------|----------------|----------------------|----------------------|
| Drain-source voltage | V_{DS} | -100 | V | |
| Gate-source voltage | V_{GS} | ± 20 | | |
| Continuous drain current ($T_J = 175$ °C) ^b | I_D | $T_C = 25$ °C | -37.1 ^a | |
| | | $T_C = 125$ °C | -31 ^a | |
| | | $T_A = 25$ °C | -9.2 ^{b, c} | |
| | | $T_A = 125$ °C | -7.7 ^{b, c} | |
| Pulsed drain current | I_{DM} | -40 | A | |
| Continuous source current (diode conduction) | I_S | $T_C = 25$ °C | | -50 ^a |
| | | $T_A = 25$ °C | | -6.9 ^{b, c} |
| Avalanche current | I_{AS} | -35 | | mJ |
| Single pulse avalanche energy | E_{AS} | 61 | | |
| Maximum power dissipation | P_D | $T_C = 25$ °C | 136 | |
| | | $T_C = 70$ °C | 95 | |
| | | $T_A = 25$ °C | 8.3 ^{b, c} | |
| | | $T_A = 70$ °C | 5.8 ^{b, c} | |
| Operating junction and storage temperature range | T_J, T_{stg} | -55 to +175 | °C | |

THERMAL RESISTANCE RATINGS

| PARAMETER | SYMBOL | TYPICAL | MAXIMUM | UNIT |
|----------------------------------|------------|---------------|---------|------|
| Junction-to-ambient ^a | R_{thJA} | $t \leq 10$ s | 15 | 18 |
| | | Steady state | 40 | 50 |
| Junction-to-case (drain) | R_{thJC} | 0.85 | 1.1 | °C/W |

Note

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 10$ s
- Maximum under steady state conditions is 40 °C/W



| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | | | | | |
|---|--------------------------------------|---|-----------|----------------|---------------------|-------|---------------------|-----------|----------------|-----|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT | | | | |
| Static | | | | | | | | | | |
| Drain-source breakdown voltage | V _{DS} | V _{GS} = 0 V, I _D = -250 μA | -100 | - | - | V | | | | |
| VDS temperature coefficient | ΔV _{DS} /T _J | I _D = -250 μA | | -109 | - | mV/°C | | | | |
| VGS(th) temperature coefficient | ΔV _{GS(th)} /T _J | | | 5.9 | - | | | | | |
| Gate-source threshold voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = -250 μA | -1 | - | -3 | V | | | | |
| Gate-source leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ±20 V | - | - | ±100 | nA | | | | |
| Zero gate voltage drain current | I _{DSS} | V _{DS} = -100 V, V _{GS} = 0 V | - | - | -1 | μA | | | | |
| | | V _{DS} = -100 V, V _{GS} = 0 V, T _J = 55 °C | - | - | -10 | | | | | |
| On-state drain current ^a | I _{D(on)} | V _{DS} ≥ 5 V, V _{GS} = -10 V | -40 | - | - | A | | | | |
| Drain-source on-state resistance ^a | R _{DS(on)} | V _{GS} = -10 V, I _D = -9.2 A | - | 0.036 | 0.043 | Ω | | | | |
| | | V _{GS} = -4.5 V, I _D = -7.7 A | - | 0.040 | 0.048 | | | | | |
| Forward transconductance ^a | g _{fs} | V _{DS} = -15 V, I _D = -9.2 A | - | 38 | - | S | | | | |
| Dynamic ^b | | | | | | | | | | |
| Input capacitance | C _{iss} | V _{DS} = -50 V, V _{GS} = 0 V, f = 1 MHz | - | 4600 | - | pF | | | | |
| Output capacitance | C _{oss} | | - | 230 | - | | | | | |
| Reverse transfer capacitance | C _{rss} | | - | 175 | - | | | | | |
| Total gate charge | Q _g | V _{DS} = -50 V, V _{GS} = -10 V, I _D = -9.2 A | - | 106 | 160 | nC | | | | |
| | | V _{DS} = -50 V, V _{GS} = -4.5 V, I _D = -9.2 A | - | 54 | 81 | | | | | |
| | | | - | 14 | - | | | | | |
| Gate-source charge | Q _{gs} | f = 1 MHz | - | 26 | - | Ω | | | | |
| Gate-drain charge | Q _{gd} | | - | 4 | - | | | | | |
| Gate resistance | R _g | | - | 15 | 25 | | | | | |
| Turn-on delay time | t _{d(on)} | V _{DD} = -50 V, R _L = 6.5 Ω I _D ≅ -7.7 A, V _{GEN} = -10 V, R _g = 1 Ω | - | 20 | 30 | ns | | | | |
| Rise time | t _r | | - | 110 | 165 | | | | | |
| Turn-off delay time | t _{d(off)} | | - | 100 | 150 | | | | | |
| Fall time | t _f | | - | 42 | 65 | | | | | |
| Turn-on delay time | t _{d(on)} | V _{DD} = -50 V, R _L = 6.5 Ω I _D ≅ -7.7 A, V _{GEN} = -4.5 V, R _g = 1 Ω | - | 160 | 240 | ns | | | | |
| | | | Rise time | t _r | - | | 100 | 150 | | |
| | | | | | Turn-off delay time | | t _{d(off)} | - | 100 | 150 |
| | | | | | | | | Fall time | t _f | - |
| Drain-source body diode characteristics | | | | | | | | | | |
| Continuous source-drain diode current | I _S | T _C = 25 °C | - | - | -50 | A | | | | |
| Pulse diode forward current ^a | I _{SM} | | - | - | -40 | | | | | |
| Body diode voltage | V _{SD} | I _S = -7.7 A | - | -0.8 | -1.2 | V | | | | |
| Body diode reverse recovery time | t _{rr} | I _F = -7.7 A, di/dt = 100 A/μs, T _J = 25 °C | - | 60 | 90 | ns | | | | |
| Body diode reverse recovery charge | Q _{rr} | | - | 150 | 225 | nC | | | | |
| Reverse recovery fall time | t _a | | - | 46 | - | ns | | | | |
| Reverse recovery rise time | t _b | | - | 14 | - | | | | | |

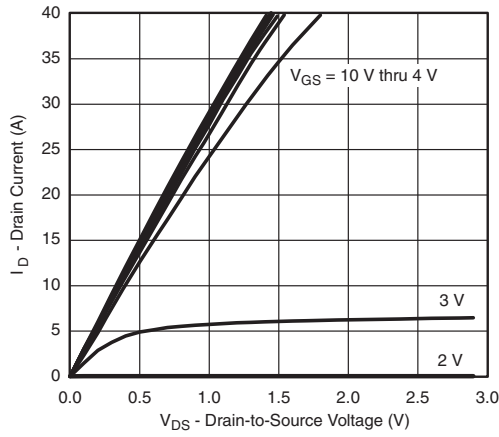
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing

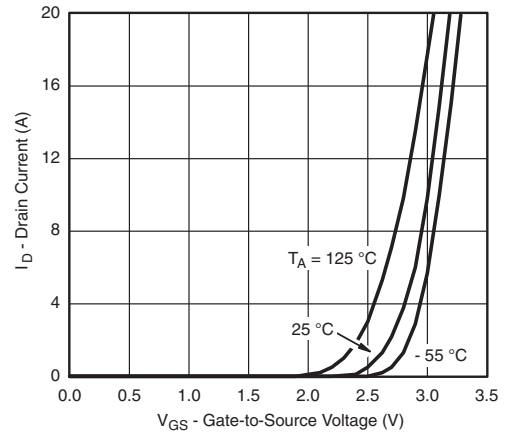
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



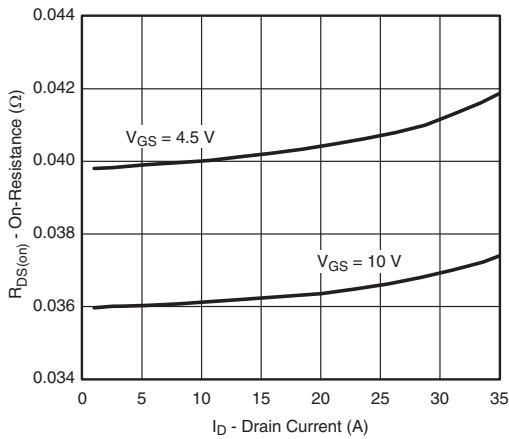
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



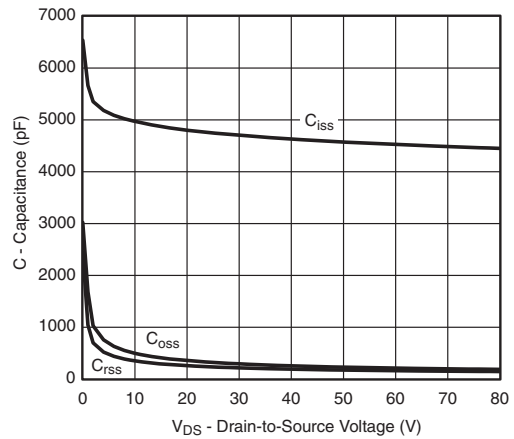
Output Characteristics



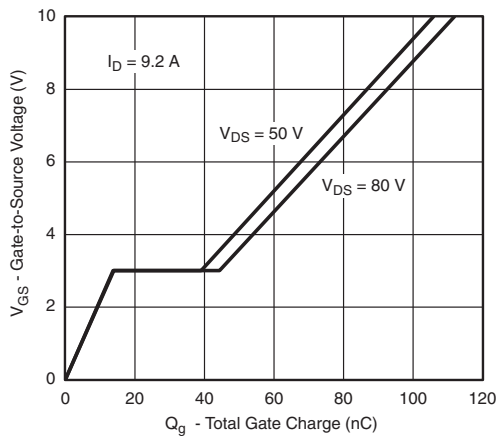
Transfer Characteristics



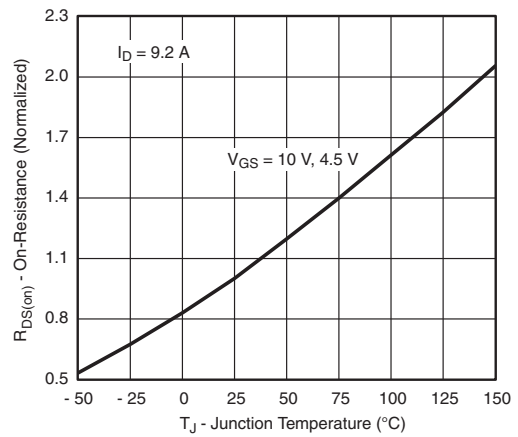
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



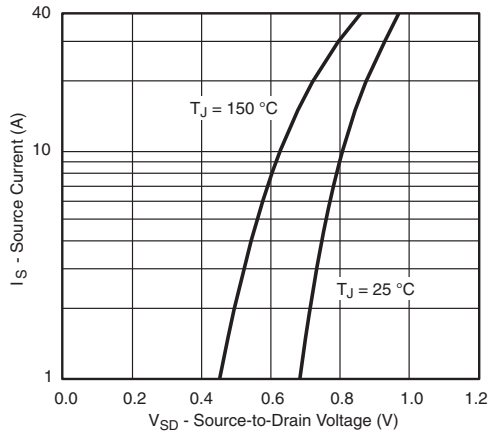
Gate Charge



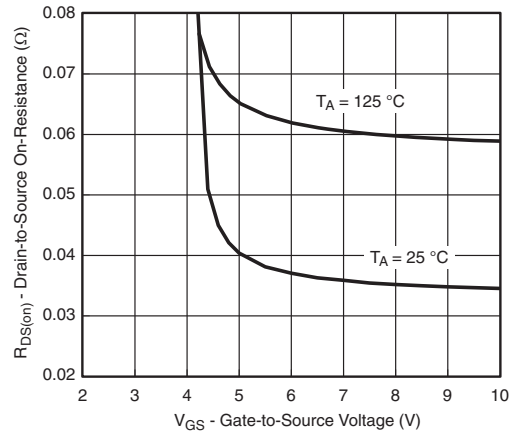
On-Resistance vs. Junction Temperature



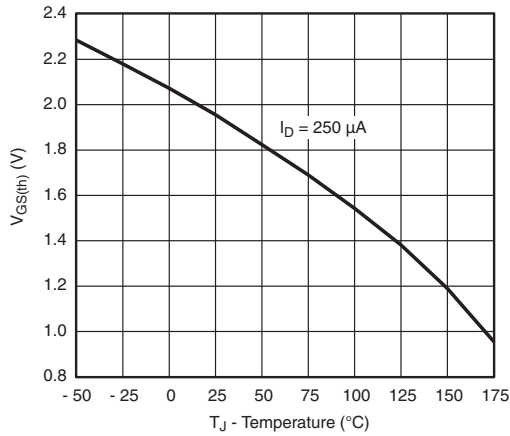
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



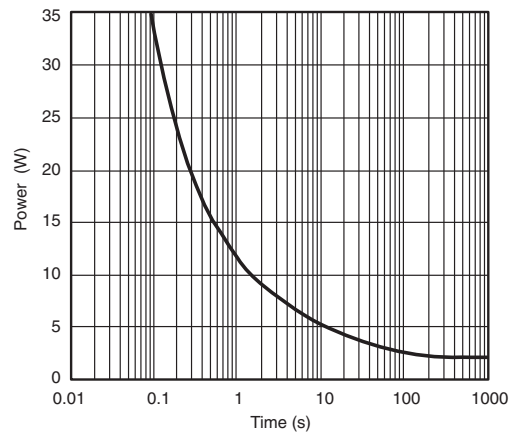
Source-Drain Diode Forward Voltage



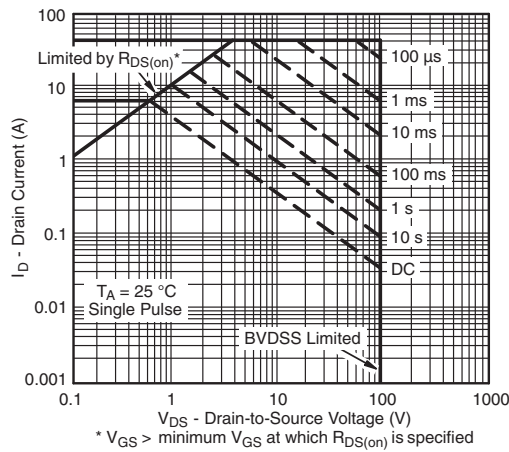
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



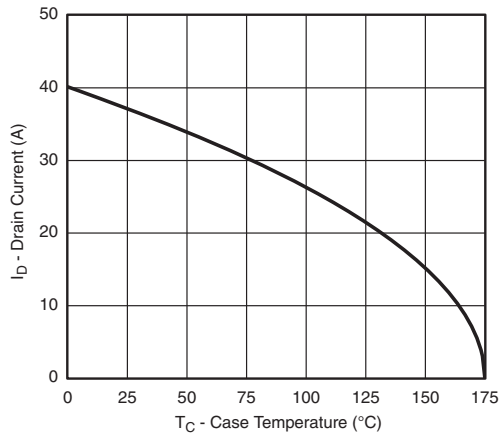
Single Pulse Power, Junction-to-Ambient



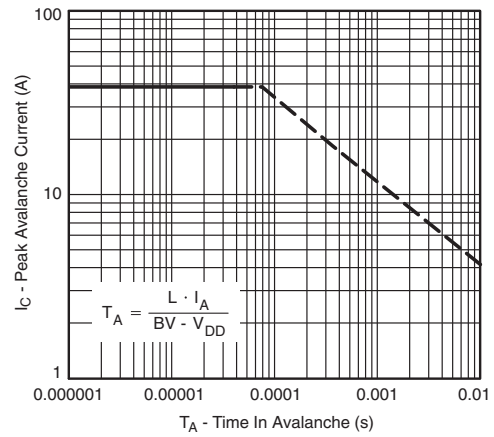
Safe Operating Area, Junction-to-Ambient



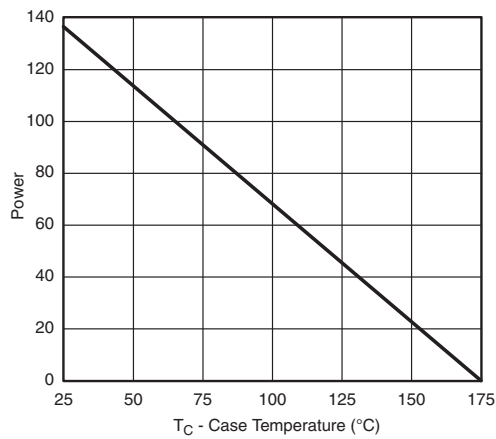
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a



Single Pulse Avalanche Capability



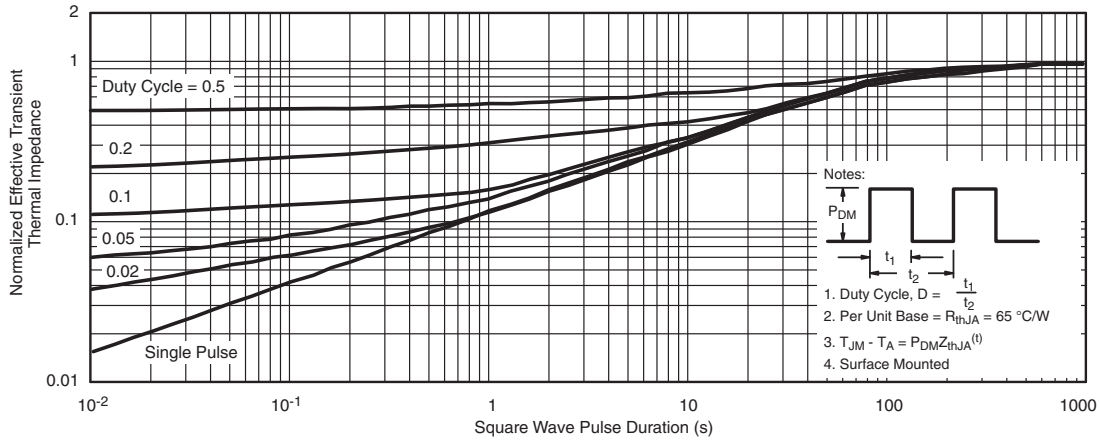
Single Pulse Power, Junction-to-Ambient

Note

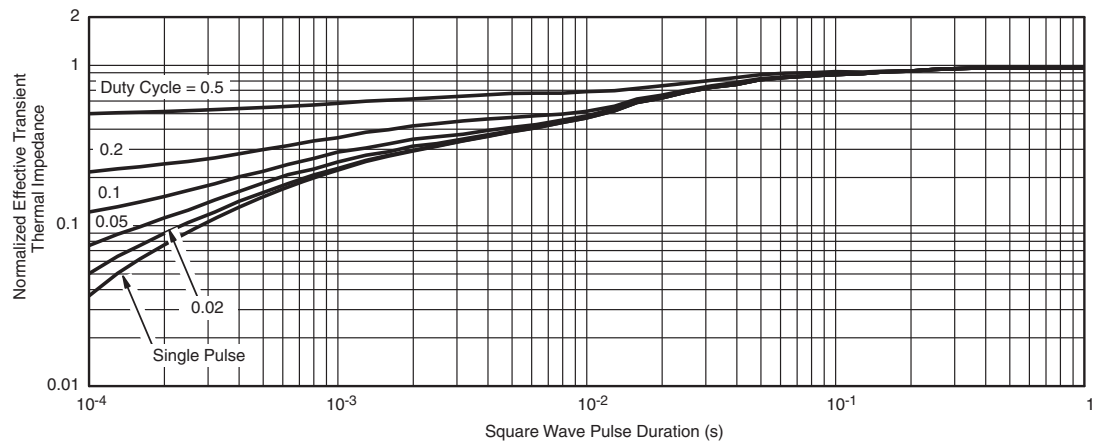
- a. The power dissipation P_D is based on $T_J \text{ max.} = 175 \text{ }^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y



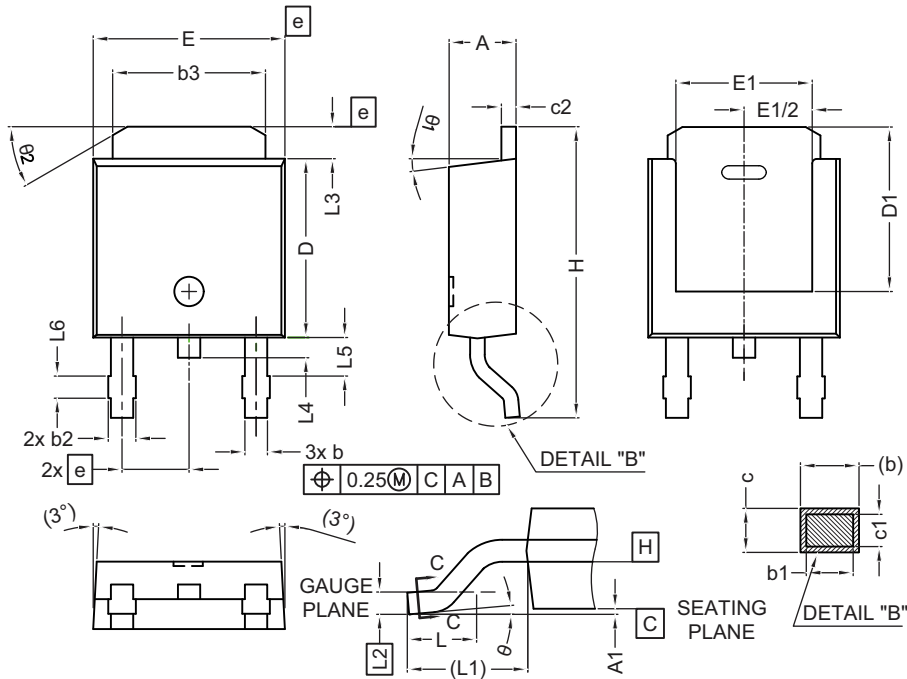
| MILLIMETERS | | |
|-------------|----------|-------|
| DIM. | MIN. | MAX. |
| A | 2.18 | 2.38 |
| A1 | - | 0.127 |
| b | 0.64 | 0.88 |
| b2 | 0.76 | 1.14 |
| b3 | 4.95 | 5.46 |
| C | 0.46 | 0.61 |
| C2 | 0.46 | 0.89 |
| D | 5.97 | 6.22 |
| D1 | 4.10 | - |
| E | 6.35 | 6.73 |
| E1 | 4.32 | - |
| H | 9.40 | 10.41 |
| e | 2.28 BSC | |
| e1 | 4.56 BSC | |
| L | 1.40 | 1.78 |
| L3 | 0.89 | 1.27 |
| L4 | - | 1.02 |
| L5 | 1.01 | 1.52 |

Note

- Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



| MILLIMETERS | | |
|-------------|----------|-------|
| DIM. | MIN. | MAX. |
| A | 2.18 | 2.39 |
| A1 | - | 0.13 |
| b | 0.65 | 0.89 |
| b1 | 0.64 | 0.79 |
| b2 | 0.76 | 1.13 |
| b3 | 4.95 | 5.46 |
| c | 0.46 | 0.61 |
| c1 | 0.41 | 0.56 |
| c2 | 0.46 | 0.60 |
| D | 5.97 | 6.22 |
| D1 | 5.21 | - |
| E | 6.35 | 6.73 |
| E1 | 4.32 | - |
| e | 2.29 BSC | |
| H | 9.94 | 10.34 |

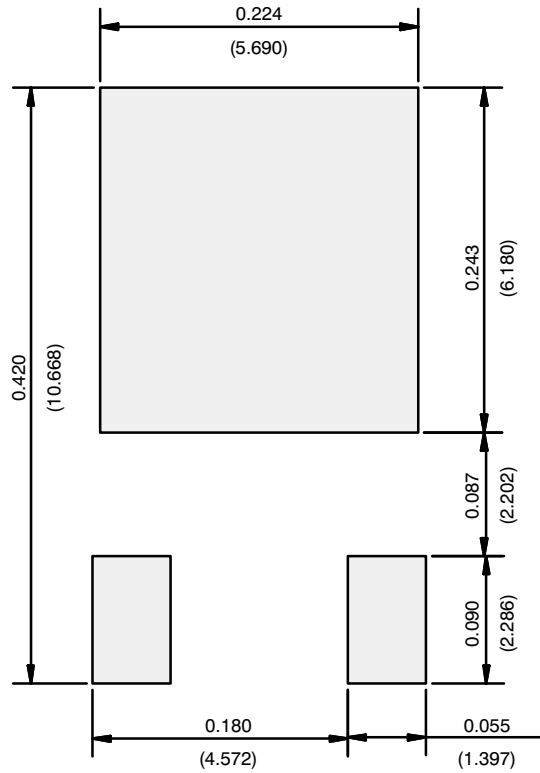
| MILLIMETERS | | |
|-------------|-----------|------|
| DIM. | MIN. | MAX. |
| L | 1.50 | 1.78 |
| L1 | 2.74 ref. | |
| L2 | 0.51 BSC | |
| L3 | 0.89 | 1.27 |
| L4 | - | 1.02 |
| L5 | 1.14 | 1.49 |
| L6 | 0.65 | 0.85 |
| θ | 0° | 10° |
| θ1 | 0° | 15° |
| θ2 | 25° | 35° |

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022
 DWG: 5347

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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